NSN 5961-01-241-7151

Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-241-7151 **Inclosure Material:** Metal **Overall Length:** 3.327 inches **End Application:** 1430-01-111-2328 **Mounting Facility Quantity:** Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-93 **Electrode Internally-electrically Connected To Case:** Anode **Mounting Method:** Threaded stud **Overall Width Across Flats:** Between 1.218 inches and 1.250 inches **Thread Size:** 0.750 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 1200.0 nonrepetitive peak reverse voltage, peak total value and 1000.0 repetitive peak reverse voltage, peak total value **Current Rating Per Characteristic:** 4250.00 amperes source cutoff current peak and 235.00 amperes source cutoff current outside diameter and 150.00 amperes forward current, average **Power Rating Per Characteristic:** 10.0 watts small-signal input power, common-collector blank and 2.0 watts small-signal input power, common-collector universal **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius junction **Test Data Document:** 18876-11437296 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Thread Series Designator:** Unf **Terminal Type And Quantity:** 1 threaded stud and 3 insulated wire lead w/terminal lug Shelf Life: N/a **Unit Of Measure:**

Fiig: A110a0

No

Demilitarization: